



**UPS Transistor U2010, PROJECT NO-
P8041, DWG POS:TR1-TR2 □ Type:
SKM 300 GB 123 D**

URL:<https://www.sxplc.com/ups-transistor-u2010-project-no-p8041-dwg-pos-tr1-tr2-type-skm-300-gb-123-d>

Product data sheet

Features

- MOS input (voltage controlled)
- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low

temperature dependence

- High short circuit capability,

self limiting to $6 * I_{cnom}$

- Latch-up free

- Fast & soft inverse CAL

diodes)

- Isolated copper baseplate

using DCB Direct Copper Bonding Technology

- Large clearance (12 mm) and

creepage distances (20 mm).

Typical Applications: → B6-153

- Switching, not for linear use

- AC-inverter drives

- UPS

1) $T_{case} = 25\text{ °C}$, unless otherwise

specified 2) $I_F = -I_C$, $V_R = 600\text{ V}$,

- $di_F/dt = 2000\text{ A}/\mu\text{s}$, $V_{GE} = 0\text{ V}$

3) Use $V_{GEoff} = -5 \dots -15\text{ V}$

5) see fig. 2 + 3; $R_{Goff} = 4,7 \Omega$

6) The free-wheeling diodes of

the GAL and GAR types have

the data of the inverse diodes

of SKM 400 GA 123 D

8) CAL = Controlled Axial Lifetime

Technology.

